

1. Record Nr.	UNINA9910830036703321
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Titolo	Defects in Organic Semiconductors and Devices
Pubbl/distr/stampa	Newark : , : John Wiley & Sons, Incorporated, , 2023 ©2023
ISBN	1-394-22945-3 1-394-22943-7
Descrizione fisica	1 online resource (279 pages)
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
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